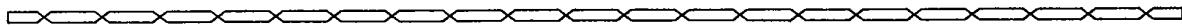


LT011PS

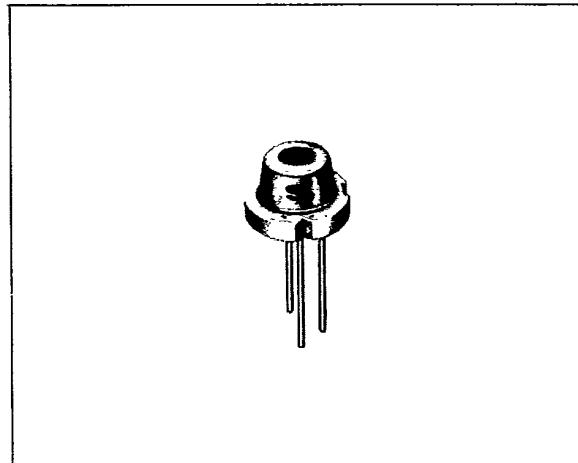


Features

- Compact (diameter: 5.6 mm)
- Wavelength: 840nm
- Single transverse mode

Applications

- Measurement instruments
- Analysis instruments



Absolute Maximum Ratings

(Tc=25°C)

Parameter	Symbol	Ratings	Units
Optical power output	Po	5	mW
Reverse voltage PIN	V _R	2	V
		30	
Operating temperature* ¹	Topr	-10 ~ +60	°C
Storage temperature* ¹	Tstg	-40 ~ +85	°C
Soldering temperature* ²	Tsol	260 (less than 5 seconds)	°C

*1 Case temperature *2 At point 1.6 mm from lead base

Electro-optical Characteristics*¹

(Tc=25°C)

Parameter	Symbol	Condition	Ratings			Units	
			MIN	TYP	MAX		
Threshold current	I _{th}	—	—	50	70	mA	
Operating current	I _{op}	Po=3mW	—	60	85	mA	
Operating voltage	V _{op}	Po=3mW	—	1.75	2.0	V	
Wavelength* ²	λ _p	Po=3mW	825	840	850	nm	
Monitor current	I _m	Po=3mW V _R =15V	0.08	0.20	0.42	mA	
Radiation characteristics	Angle* ³	Parallel to junction	θ //	Po=3mW	8.5	12	deg
		Perpendicular to junction	θ ⊥	Po=3mW	25	40	deg
Emission point accuracy	Angle	Ripple	—	Po=3mW	—	±20	%
		Δϕ //	—	Po=3mW	—	±2	deg
	Position	Δϕ ⊥	—	Po=3mW	—	±3	deg
		Δx, Δy, Δz	—	—	—	±80	μm
Differential efficiency	η	2mW I _F (3mW) - I _F (1mW)	0.12	0.25	0.60	mW/mA	

*1 Initial value

*2 Single transverse mode

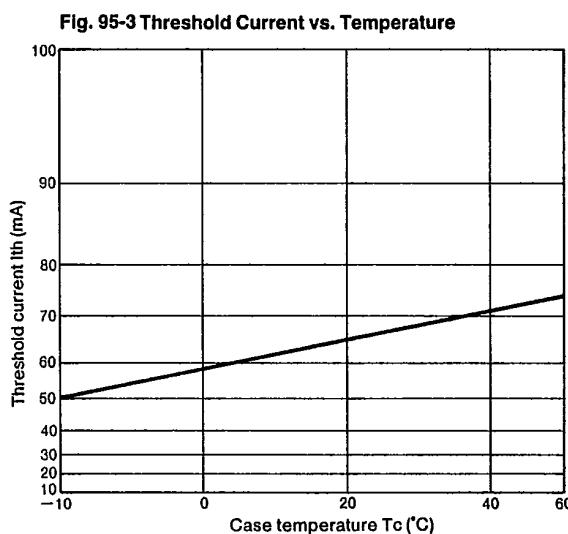
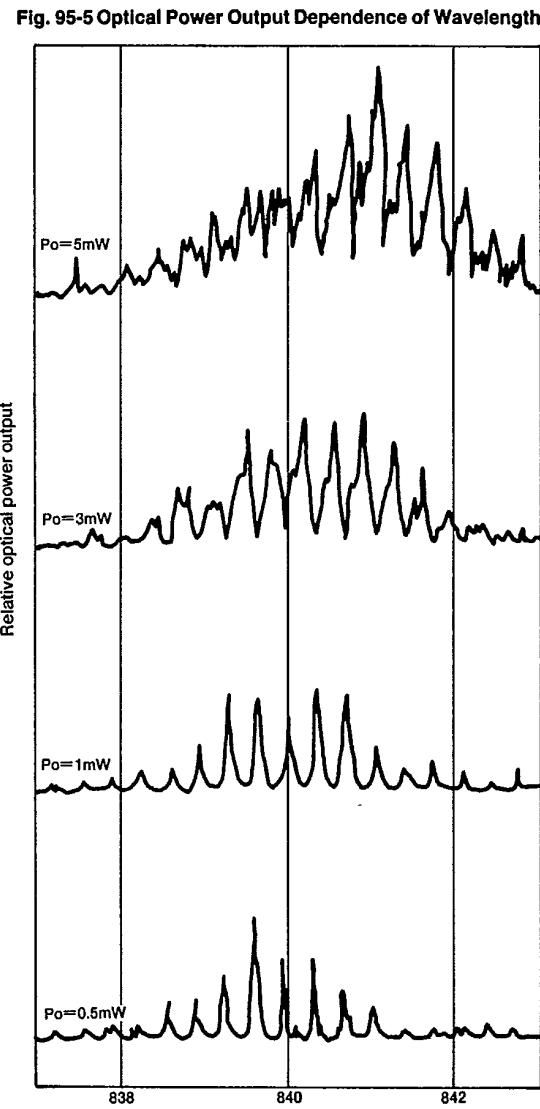
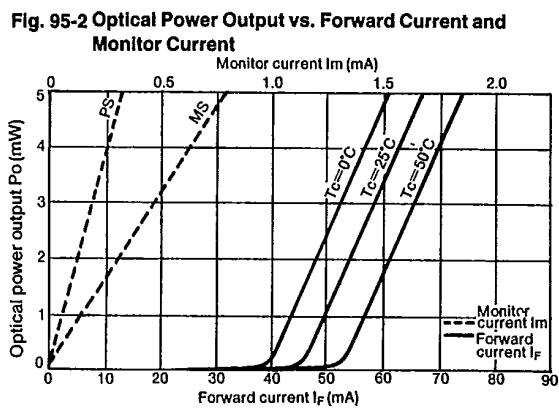
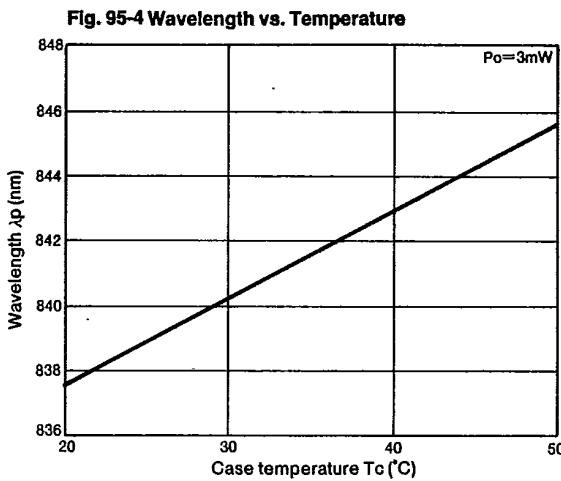
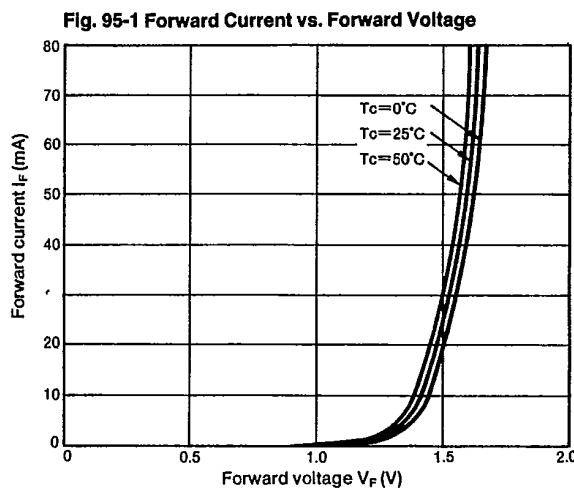
*3 Angle at 50% peak intensity (full width at half-maximum)

Electrical Characteristics of Photodiode

(Tc=25°C)

Parameter	Symbol	Condition	Ratings			Units
			MIN	TYP	MAX	
Sensitivity	S	V _R =15V	—	0.07	—	mA/mW
Dark current	I _D	V _R =15V	—	—	150	nA
Terminal capacitance	C _t	V _R =15V	—	9	—	pF

LT011 Series Characteristics Diagrams



Note: All data on this page is typical only, and is not intended as a specification. The shape of these curves can be used as a general reference, but the actual characteristics will vary from device to device.